NSN 5962-01-226-3926

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View Online at https://aerobasegroup.com/nsn/5962-01-226-3926 **Body Length:** 0.840 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 794.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** An/bps14to15e **Features Provided:** Hermetically sealed and burn in and programmable and bipolar and schottky **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 10 input **Case Outline Source And Designator:** D-2 mil-m-38510 **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source **Time Rating Per Chacteristic:** 85.00 nanoseconds propagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to low level output **Memory Device Type:** Prom **Memory Capacity:** Unknown

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

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